Switch-mode Schottky Power Rectifier

Surface Mount Power Package

MBRB1045G, MBRD1045G, SBRB1045G, SBRD81045T4G

This series of Power Rectifiers employs the Schottky Barrier principle in a large metal-to-silicon power diode. State-of-the-art geometry features epitaxial construction with oxide passivation and metal overlay contact. Ideally suited for use in low voltage, high frequency switching power supplies, free wheeling diodes, and polarity protection diodes.

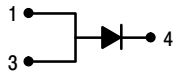
Features

- Guardring for Stress Protection
- Low Forward Voltage
- 175 °C Operating Junction Temperature
- Epoxy Meets UL 94 V−0 @ 0.125 in
- Short Heat Sink Tab Manufactured-Not Sheared!
- SBRB and SBRD8 Prefixes for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

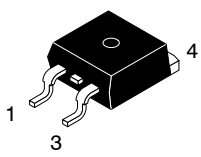
Mechanical Characteristics:

- Case: Epoxy, Molded, Epoxy Meets UL 94 V−0
- Weight: 1.7 grams for D^2PAK (approximately)
  0.4 grams for DPAK (approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead and Mounting Surface Temperature for Soldering Purposes: 260 °C Max. for 10 Seconds
- Device Meets MSL1 Requirements
- ESD Ratings:
  - Machine Model = C (> 400 V)
  - Human Body Model = 3B (> 8000 V)

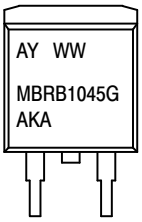
SCHOTTKY BARRIER RECTIFIER 10 AMPERES, 45 VOLTS



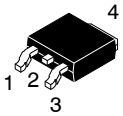
MARKING DIAGRAM



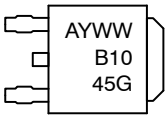
D^2PAK−3
CASE 418B



A	= Assembly Location
Y	= Year
WW	= Work Week
MBRB1045	= Device Code
G	= Pb−Free Package
AKA	= Diode Polarity



DPAK
CASE 369C



A	= Assembly Location
Y	= Year
WW	= Work Week
B1045	= Device Code
G	= Pb−Free Package

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 3 of this data sheet.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	45	V
Average Rectified Forward Current, T_C = 135 °C	$I_{F(AV)}$	10	A
Peak Repetitive Forward Current (Square Wave, Duty = 0.5) T_C = 135 °C	I_{FRM}	20	A
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I_{FSM}	150 (MBRB/SBRB) 70 (MBRD/SBRD)	A
Operating Junction and Storage Temperature Range (Note 1)	T_J, T_{stg}	−65 to +175	°C
Voltage Rate of Change (Rated V_R)	dv/dt	10000	V/μs

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. The heat generated must be less than the thermal conductivity from Junction−to−Ambient: $dP_D/dT_J < 1/R_{\theta JA}$.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Thermal Resistance, (MBRB1045G) Junction−to−Case (Note 2) Junction−to−Ambient (Note 2) (MBRD1045G) Junction-to-Case (Note 2) Junction-to-Ambient (Note 2)	 $R_{\theta JC}$ $R_{\theta JA}$ $R_{\theta JC}$ $R_{\theta JA}$	 1.0 50 2.43 68	°C/W

2. When mounted using minimum recommended pad size on FR−4 board.

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Maximum Instantaneous Forward Voltage (Note 3) (I_F = 10 Amps, T_J = 125 °C) (I_F = 20 Amps, T_J = 125 °C) (I_F = 20 Amps, T_J = 25 °C)	V_F	 0.57 0.72 0.84	V
Maximum Instantaneous Reverse Current (Note 3) (Rated dc Voltage, T_J = 125 °C) (Rated dc Voltage, T_J = 25 °C)	I_R	 15 0.1	mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2.0%

ORDERING INFORMATION

Device	Package	Shipping†
SBRB1045T4G	D^2PAK–3 (Pb–Free)	800 Units / Tape & Reel
MBRD1045T4G	DPAK (Pb–Free)	2,500 Units / Tape & Reel

DISCONTINUED (Note 4)

Device	Package	Shipping†
MBRB1045G	D^2PAK–3 (Pb–Free)	50 Units / Rail
SBRB1045G		50 Units / Rail
MBRB1045T4G		800 Units / Tape & Reel
MBRD1045G	DPAK (Pb–Free)	50 Units / Rail
SBRD81045T4G	DPAK (Pb–Free)	2,500 Units / Tape & Reel
SSBRD81045T4G		2,500 Units / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

4. **DISCONTINUED:** This device is not recommended for new design. Please contact your **onsemi** representative for information. The most current information on this device may be available on www.onsemi.com.

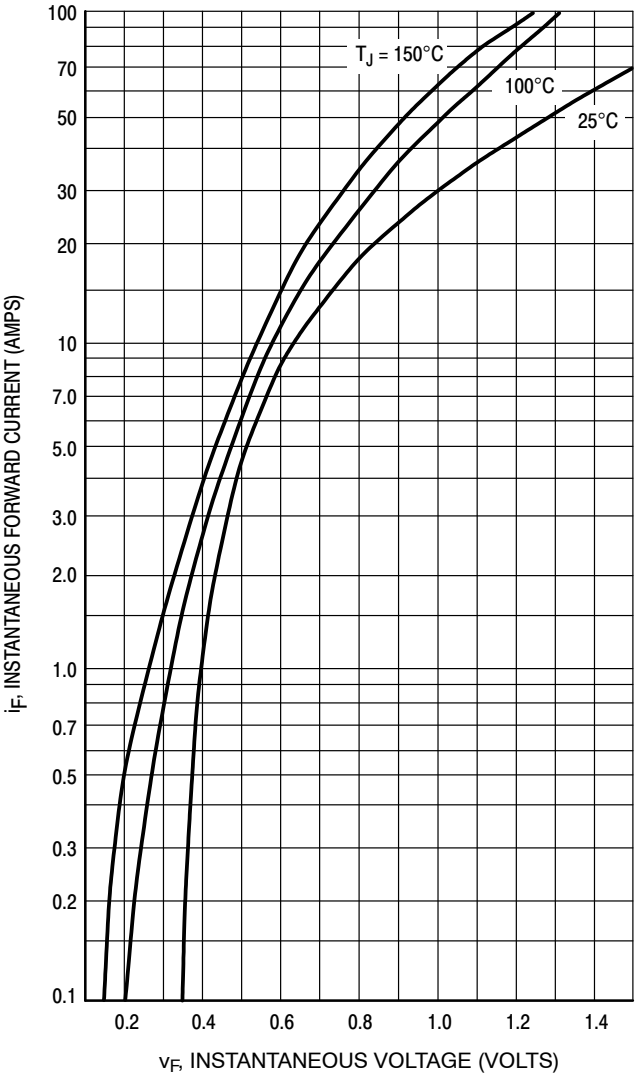


Figure 1. Maximum Forward Voltage

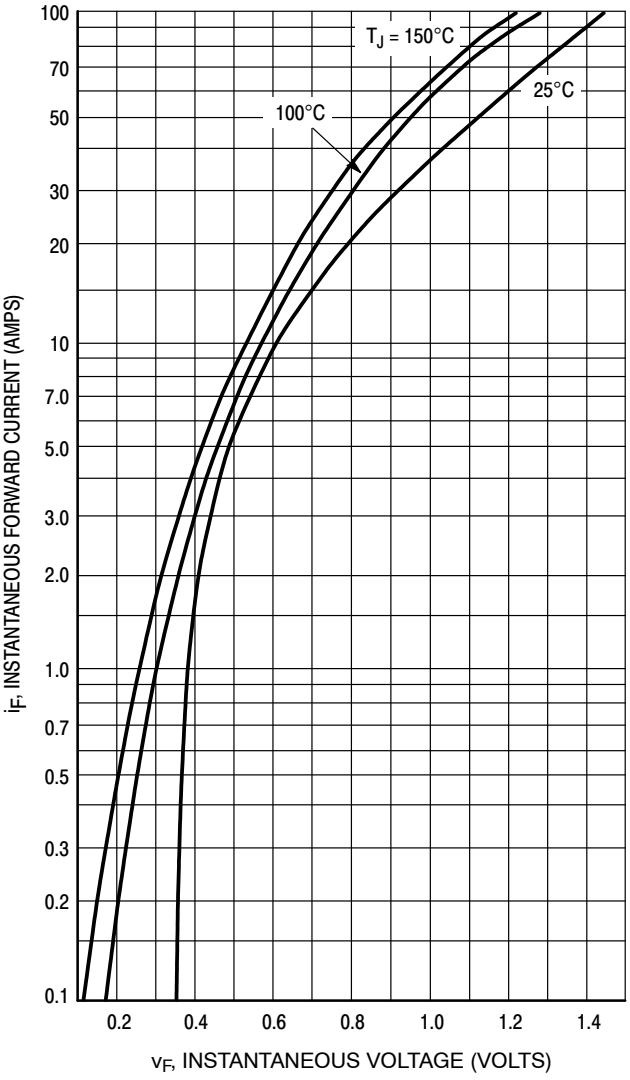


Figure 2. Typical Forward Voltage

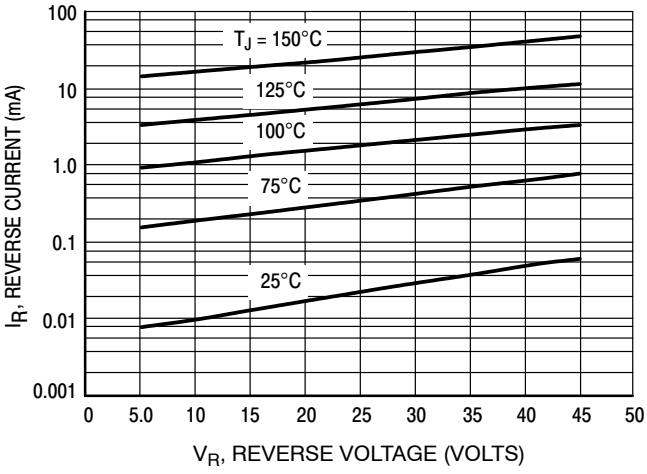


Figure 3. Maximum Reverse Current

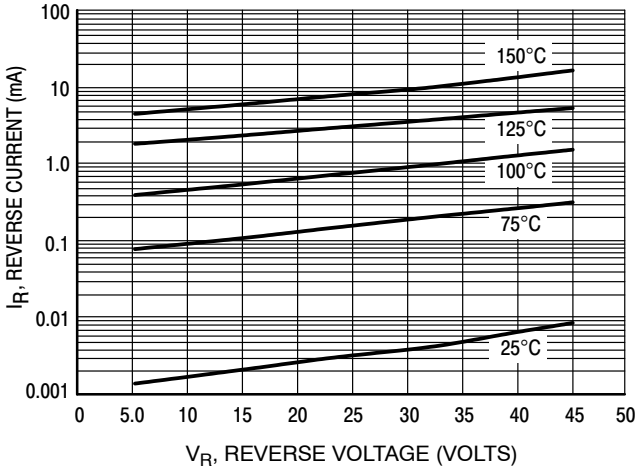


Figure 4. Typical Reverse Current

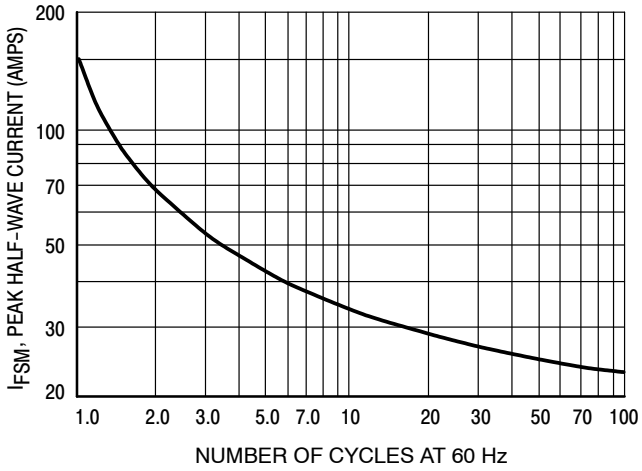


Figure 8. Maximum Surge Capability

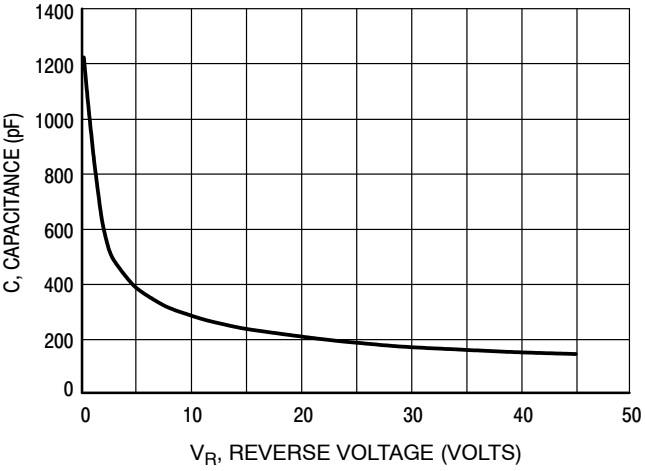


Figure 5. Typical Capacitance

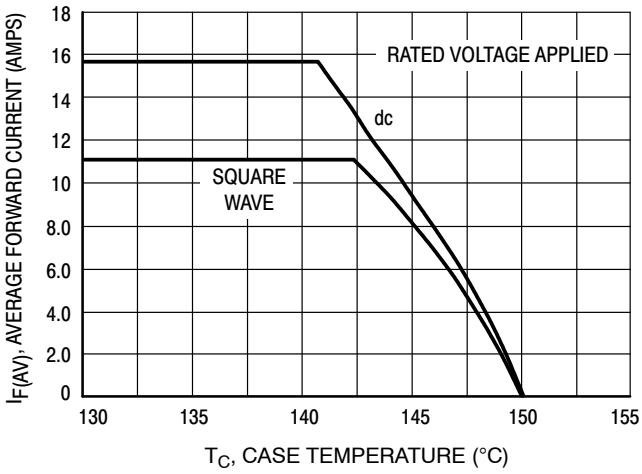


Figure 6. Current Derating, Case,
$R_{\theta JC}$ = 1.0 °C/W

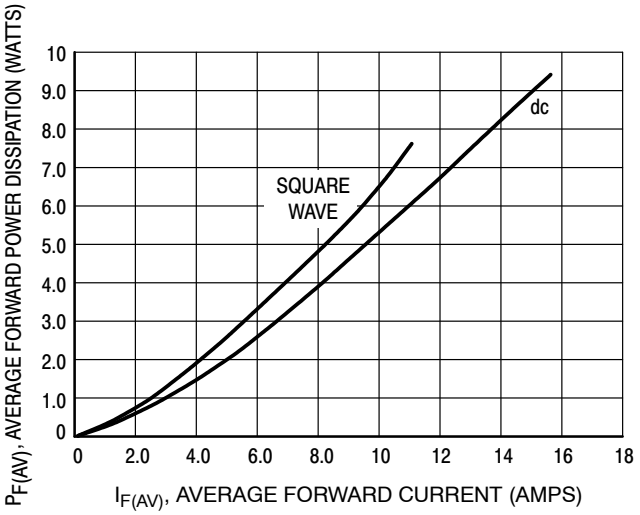
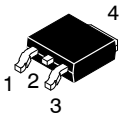


Figure 7. Forward Power Dissipation

REVISION HISTORY

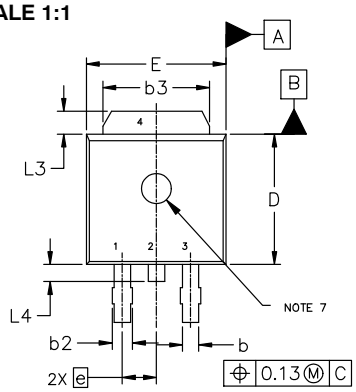
Revision	Description of Changes	Date
12	MBRB1045G, SBRB1045G, MBRB1045T4G, MBRD1045G, SBRD81045T4G, SS-BRD81045T4G OPN Marked as Discontinued + Rebranded the Data Sheet to onsemi format	7/1/2025



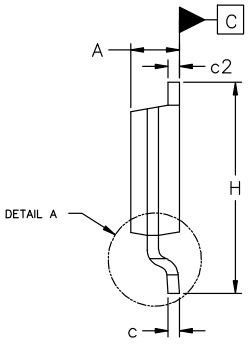
SCALE 1:1

DPAK3 6.10x6.54x2.28, 2.29P
CASE 369C
ISSUE H

DATE 15 JUL 2025

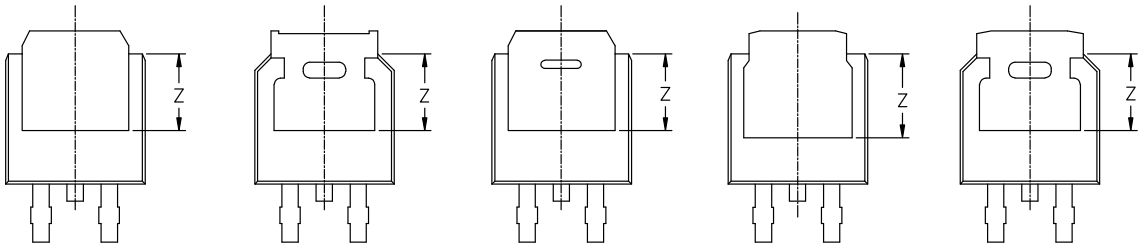


TOP VIEW



SIDE VIEW

MILLIMETERS			
DIM	MIN	NOM	MAX
A	2.18	2.28	2.38
A1	0.00	---	0.13
b	0.63	0.76	0.89
b2	0.72	0.93	1.14
b3	4.57	5.02	5.46
c	0.46	0.54	0.61
c2	0.46	0.54	0.61
D	5.97	6.10	6.22
E	6.35	6.54	6.73
e	2.29 BSC		
H	9.40	9.91	10.41
L	1.40	10.10	1.78
L1	2.90 REF		
L2	0.51 BSC		
L3	0.89	---	1.27
L4	---	---	1.01
Z	3.93	---	---

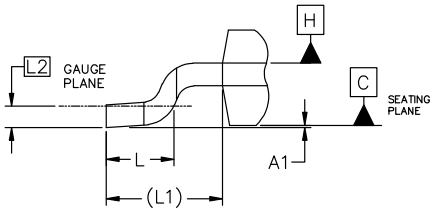


BOTTOM VIEW

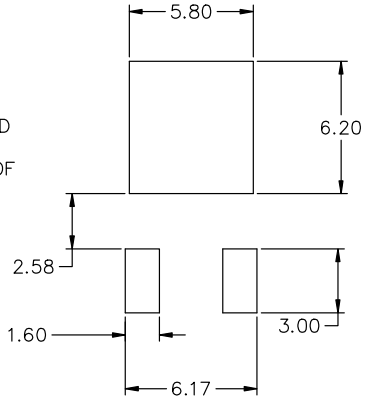
ALTERNATE CONSTRUCTIONS

NOTES:

1. DIMENSIONING AND TOLERANCING ASME Y14.5M, 2018.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3, AND Z.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15mm PER SIDE.
5. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
6. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.
7. OPTIONAL MOLD FEATURE.



DETAIL A
ROTATED 90° CW



RECOMMENDED MOUNTING FOOTPRINT*

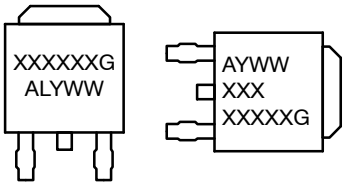
*FOR ADDITIONAL INFORMATION ON OUR PB–FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ONSEMI SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

DOCUMENT NUMBER:	**98AON10527D**	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	**DPAK3 6.10x6.54x2.28, 2.29P**	**PAGE 1 OF 2**

DPAK3 6.10x6.54x2.28, 2.29P
CASE 369C
ISSUE H

DATE 15 JUL 2025

GENERIC MARKING DIAGRAM*



IC **Discrete**

XXXXXX	= Device Code
A	= Assembly Location
L	= Wafer Lot
Y	= Year
WW	= Work Week
G	= Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 2:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

STYLE 3:
PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE

STYLE 4:
PIN 1. CATHODE
2. ANODE
3. GATE
4. ANODE

STYLE 5:
PIN 1. GATE
2. ANODE
3. CATHODE
4. ANODE

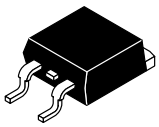
STYLE 6:
PIN 1. MT1
2. MT2
3. GATE
4. MT2

STYLE 7:
PIN 1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 8:
PIN 1. N/C
2. CATHODE
3. ANODE
4. CATHODE

STYLE 9:
PIN 1. ANODE
2. CATHODE
3. RESISTOR ADJUST
4. CATHODE

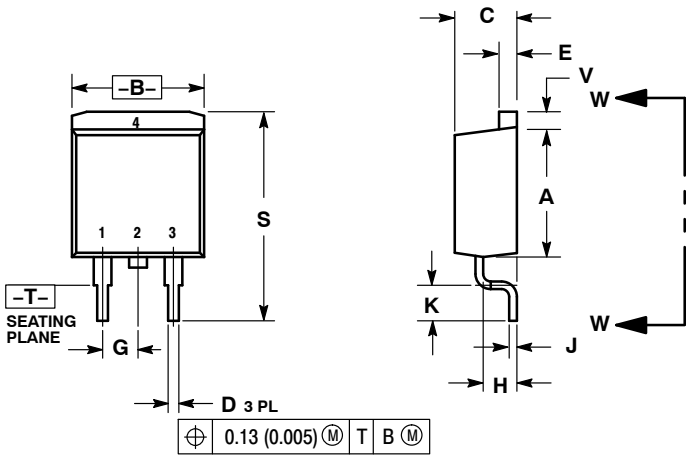
STYLE 10:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. ANODE



SCALE 1:1

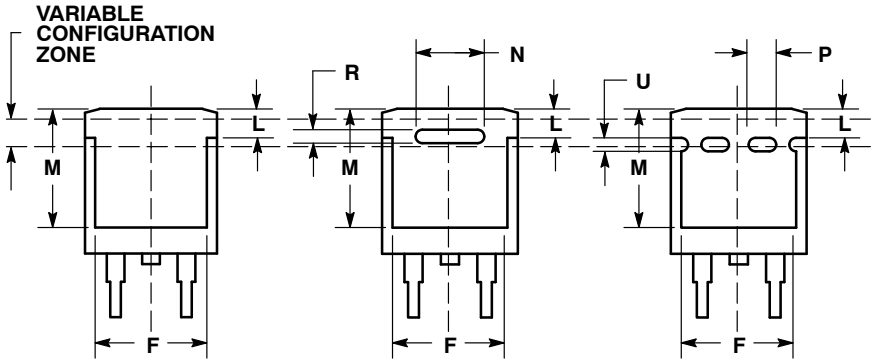
D²PAK 3
CASE 418B–04
ISSUE L

DATE 17 FEB 2015



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 418B–01 THRU 418B–03 OBSOLETE, NEW STANDARD 418B–04.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.340	0.380	8.64	9.65
B	0.380	0.405	9.65	10.29
C	0.160	0.190	4.06	4.83
D	0.020	0.035	0.51	0.89
E	0.045	0.055	1.14	1.40
F	0.310	0.350	7.87	8.89
G	0.100 BSC		2.54 BSC	
H	0.080	0.110	2.03	2.79
J	0.018	0.025	0.46	0.64
K	0.090	0.110	2.29	2.79
L	0.052	0.072	1.32	1.83
M	0.280	0.320	7.11	8.13
N	0.197 REF		5.00 REF	
P	0.079 REF		2.00 REF	
R	0.039 REF		0.99 REF	
S	0.575	0.625	14.60	15.88
V	0.045	0.055	1.14	1.40



VIEW W–W 1 | VIEW W–W 2 | VIEW W–W 3

STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 2:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

STYLE 3:
PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE

STYLE 4:
PIN 1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 5:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. ANODE

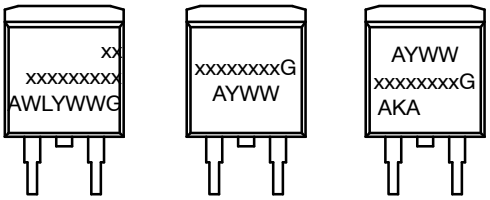
STYLE 6:
PIN 1. NO CONNECT
2. CATHODE
3. ANODE
4. CATHODE

MARKING INFORMATION AND FOOTPRINT ON PAGE 2

D²PAK 3
CASE 418B−04
ISSUE L

DATE 17 FEB 2015

GENERIC MARKING DIAGRAM*

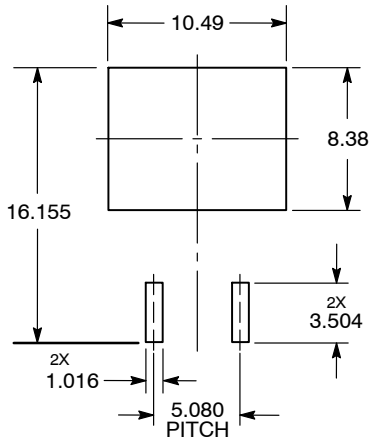


IC **Standard** **Rectifier**

xx	= Specific Device Code
A	= Assembly Location
WL	= Wafer Lot
Y	= Year
WW	= Work Week
G	= Pb−Free Package
AKA	= Polarity Indicator

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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DESCRIPTION:	**D²PAK 3**		**PAGE 2 OF 2**

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